

A1 4. (Amended) The semiconductor nonvolatile storage element according to Claim 1 or 2:

wherein an area of the second conductor layer above the ferroelectric layer is made smaller than an area of the ferroelectric layer.

5. (Amended) The semiconductor nonvolatile storage element according to Claim 1 or 2:

wherein the second conductor layer is disposed above an element isolating region of the semiconductor substrate.

6. (Amended) The semiconductor nonvolatile storage element according to Claim 1 or 2:

wherein each of the first insulator layer and the second insulator thin film comprises a layer of one material or a layer laminated with two or more of materials selected from a group consisting of SiO_2 (silicon oxide), SiN (silicon nitride), SiON (silicon oxynitride), $\text{SiO}_2\text{-SiN}$ (ON film: silicon oxide - silicon nitride), $\text{SiO}_2\text{-SiN-SiO}_2$ (ONO film: silicon oxide - silicon nitride - silicon oxide), Ta_2O_5 , SrTiO_3 , TiO_2 , $(\text{Ba}, \text{Sr})\text{TiO}_3$, Al_2O_3 , ZrO_2 , HfO_2 , Y_2O_3 , CeO_2 , CeZrO_2 and YSZ (yttrium oxide stabilized zirconium oxide).